

Silicon PNP Power Transistors

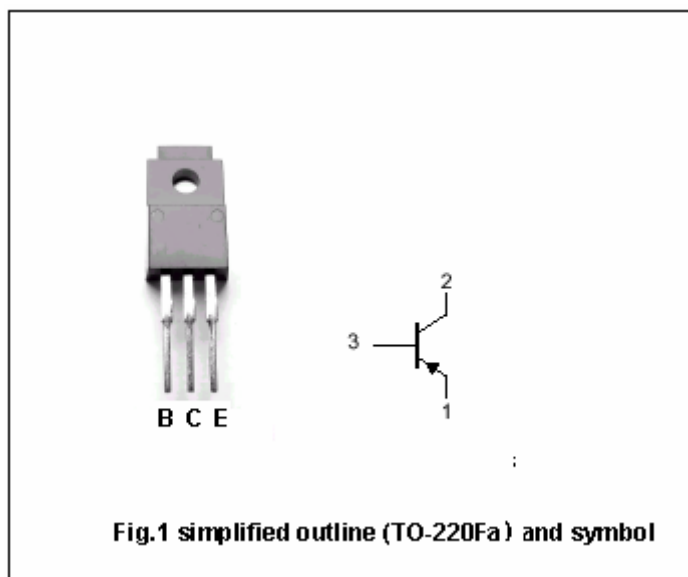
2SB1370

DESCRIPTION

- With TO-220Fa package
- $P_C=2W(T_a=25^\circ)/30W(T_C=25^\circ)$
- Low collector saturation voltage
- Wide area of safe operation

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

Absolute maximum ratings($T_a=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector -emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-3	A
I_{CM}	Collector current-peak		-6	A
P_C	Collector power dissipation	$T_a=25^\circ$	2.0	W
		$T_C=25^\circ$	30	
T_j	Junction temperature		150	$^\circ$
T_{stg}	Storage temperature		-55~150	$^\circ$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-1mA; I_B=0$	-60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-50\mu A; I_E=0$	-60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-50\mu A; I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-2A; I_B=-0.2A$			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-2A; I_B=-0.2A$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-60V; I_E=0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-4V; I_C=0$			-10	μA
h_{FE}	DC current gain	$I_C=-0.5A; V_{CE}=-5V$	100		320	
f_T	Transition frequency	$I_C=-0.5A; V_{CE}=-5V$		15		MHz
C_{OB}	Collector output capacitance	$f=1MHz; V_{CB}=10V$		80		pF

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PACKAGE OUTLINE

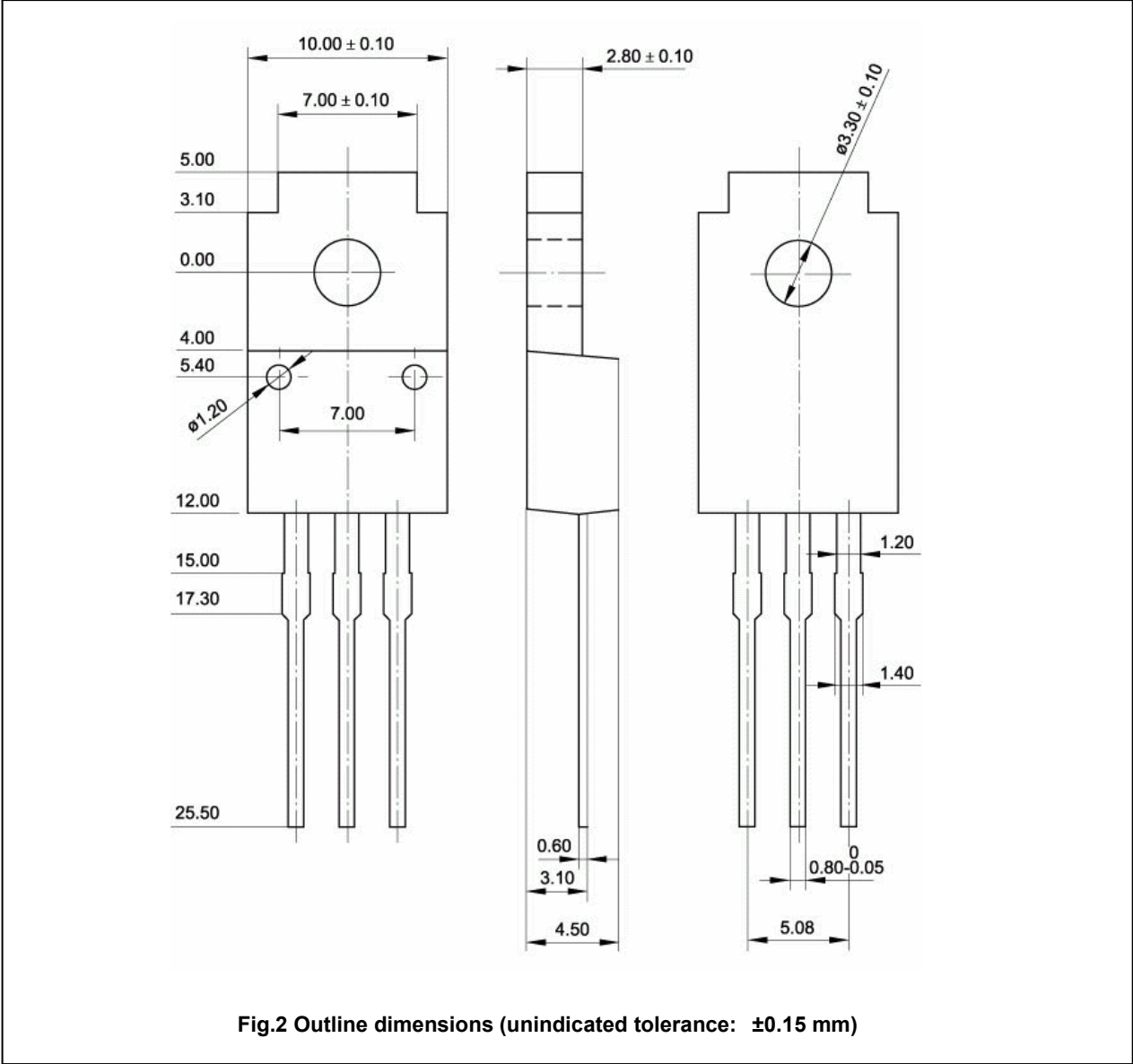


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)